



MMBT3904Q

40V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Description

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

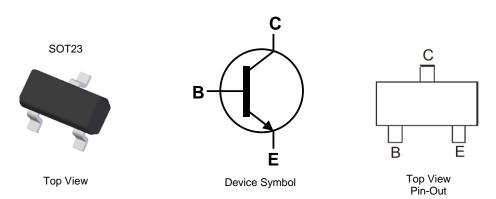
Features

- Complementary PNP Type Available (DIODES™ MMBT3906Q)
- Ideal for Medium Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES[™] MMBT3904Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 4)

Product	Package	Morking	Reel Size (inches)	Tape Width (mm)	Pac	king
Froduct	Fackage	Marking Reel Size (inches)	rape width (mm)	Qty.	Carrier	
MMBT3904Q-7-F	SOT23	K1N	7	8	3,000	Reel
MMBT3904Q-13-F	SOT23	K1N	13	8	10,000	Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

K1N	ΥM

K1N = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: J = 2022) M or M = Month (ex: 9 = September)

Date Code Key

Notes:

Date Obuc Rey												
Year	2014		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	В		J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current	Ι _C	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		310	mW	
	(Note 6)	P _D	350	THVV	
Thermal Desistance Junction to Ambient	(Note 5)	P	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	357	°C/vv	
Thermal Resistance, Junction to Leads (Note 7)		R _{θJL}	350	°C/W	
Operating and Storage Temperature Range	Operating and Storage Temperature Range			°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

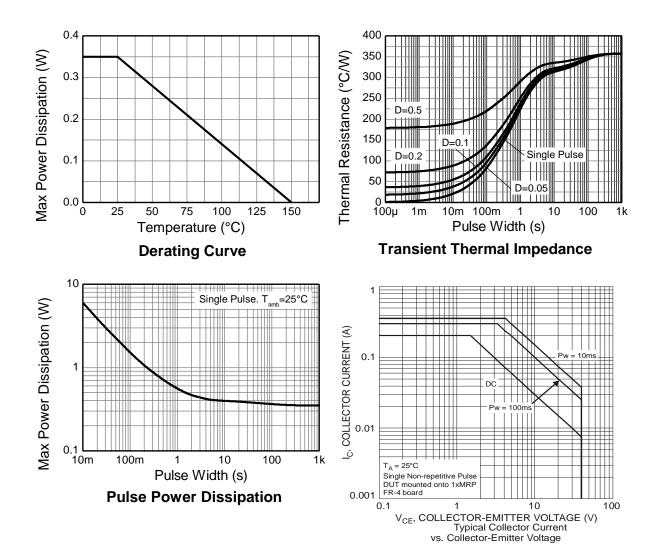
6. Same as Note 5, except the device is mounted on 15 mm x 15mm 1oz copper.

7. Thermal resistance from junction to solder-point (at the end of the leads).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





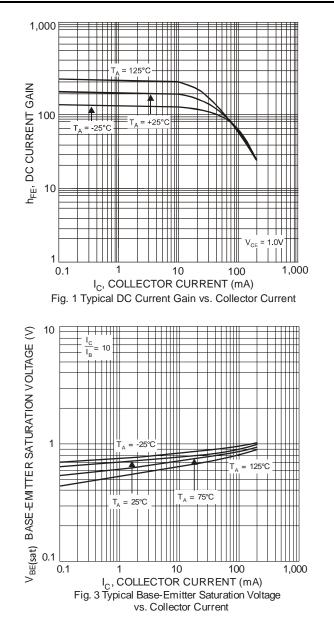
Electrical Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

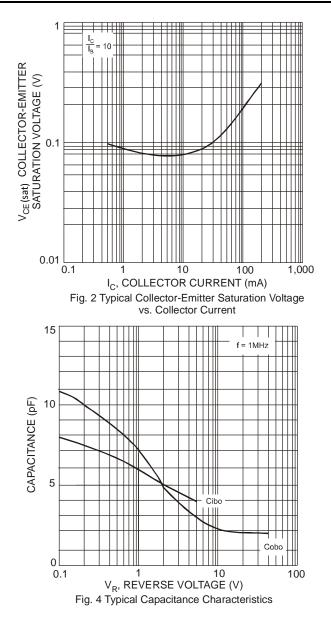
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS			1		
Collector-Base Breakdown Voltage	BVCBO	60		V	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BVCEO	40		V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0		V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector Cut-Off Current	ICEX		50	nA	$V_{CE} = 30V, V_{EB(off)} = 3.0V$
Base Cut-Off Current	I _{BL}		50	nA	$V_{CE} = 30V, V_{EB(off)} = 3.0V$
Emitter Base Cut-Off Current	I _{EBO}	_	50	nA	$V_{EB} = 6V$
Collector-Base Cut-Off Current	I _{CBO}	_	50	nA	$V_{CB} = 48V$
ON CHARACTERISTICS (Note 9)					
		40			$I_{C} = 100 \mu A, V_{CE} = 1.0 V$
		70			$I_{C} = 1.0 \text{mA}, V_{CE} = 1.0 \text{V}$
DC Current Gain	hFE	100	300		$I_{C} = 10mA, V_{CE} = 1.0V$
		60			$I_{C} = 50 \text{mA}, V_{CE} = 1.0 \text{V}$
		30			$I_{C} = 100 \text{mA}, V_{CE} = 1.0 \text{V}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.20	V	$I_{C} = 10 \text{mA}, I_{B} = 1.0 \text{mA}$
	• CE(sai)		0.30		$I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 5.0 {\rm mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.65	0.85	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 1.0 {\rm mA}$
5	· DE(Sat)	_	0.95		$I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 5.0 {\rm mA}$
SMALL SIGNAL CHARACTERISTICS			4.0	-	
Output Capacitance	Сово		4.0	pF	$V_{CB} = 5.0V, f = 1.0MHz, I_E = 0$
Input Capacitance	C _{IBO}		8.0	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_C = 0$
Input Impedance	hie	1.0	10	kΩ	-
Voltage Feedback Ratio	h _{RE}	0.5	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_C = 1.0mA,$
Small Signal Current Gain	h _{FE}	100	400		f = 1.0kHz
Output Admittance	hOE	1.0	40	μS	
Current Gain-Bandwidth Product	f⊤	300		MHz	$V_{CE} = 20V, I_C = 10mA,$ f = 100MHz
Noise Figure	NF	_	5.0	dB	$V_{CE} = 5.0V$, $I_C = 100\mu A$, $R_S = 1.0k\Omega$, $f = 1.0kHz$
SWITCHING CHARACTERISTICS	I				
Delay Time	t _d		35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Rise Time	tr		35	ns	$V_{BE(OFF)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	ts		200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	tf	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

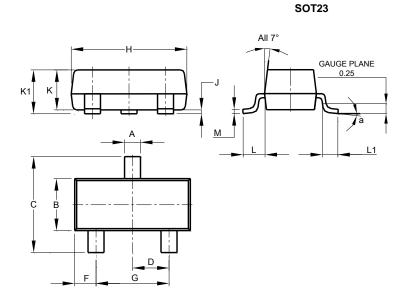






Package Outline Dimensions

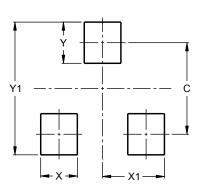
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
в	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
H	2.80	3.00	2.90					
J	0.013	0.10	0.05					
К	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

utlines.html for the latest version



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